TEXAS INSTRUMENTS
TMUX1248
JAJSLW1 – JULY 2021

TMUX1248 3Ω、低オン抵抗、 5V、 2:1 (SPDT) 汎用スイッチ 1.8V ロジック付き

1 特長

- レール・ツー・レール動作
- 双方向の信号パス
- 1.8V ロジック互換
- フェイルセーフ・ロジック
- 制御入力過電圧耐性: 5.5 V
- 低オン抵抗:3Ω
- 広い電源電圧範囲 1.08 V～5.5 V
- -40℃～+125℃ の動作温度範囲
- 低消費電流:7nA
- ブレイク・ビフォー・メイクのスイッチング動作

2 アプリケーション

- アナログおよびデジタル・スイッチング
- I^2C および SPI バスの多重化
- ラック・サーバー
- ネットワーク・インタフェース・カード (NIC)
- バーコード・スキャナー
- ビル・オートメーション
- アナログ入力モジュール
- モータ・ドライブ
- ビデオ監視
- POS システム
- デスクトップ PC
- 家電製品

3 概要

TMUX1248 は、汎用の 2 : 1 単極双投(SPDT)スイッチで、1.08V～5.5V の広い動作範囲をサポートします。このデバイスはソース(Sx)およびドレイン(D)ピンで、GND から V_{DD} までの範囲の双方向アナログおよびデジタル信号をサポートします。選択ピンの状態(SEL)は、ドレイン・ピンに接続される 2 つのソース・ピンのうちどれを制御します。さらに、TMUX1248 は消費電流が 7nA と小さいため、デバイスをホストのハンドヘルドまたは低消費電力アプリケーションで使用できます。

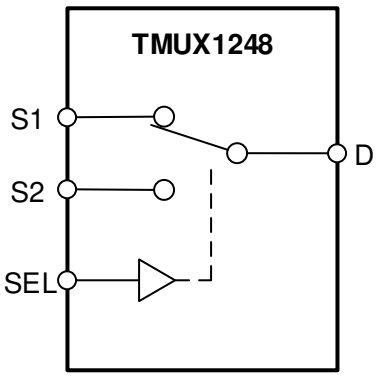
ブレーク・ビフォア・メイク のスイッチングにより、両方のソース・ピンが同時にイネーブルになることが防止されます。この機能により、スイッチング・イベント中のソース信号が短絡しないようにすることで、システムの堅牢性が向上します。

すべてのロジック入力は 1.8V ロジック互換 のスレッショルドで、低電圧ロジック信号での動作が可能です。フェイルセーフ・ロジック 回路により、電源ピンよりも前に制御ピンに電圧が印加されるか、電源ピンよりも最大 5.5V までの高電圧で電圧が印加されるため、デバイスへの損傷の可能性が避けられます。

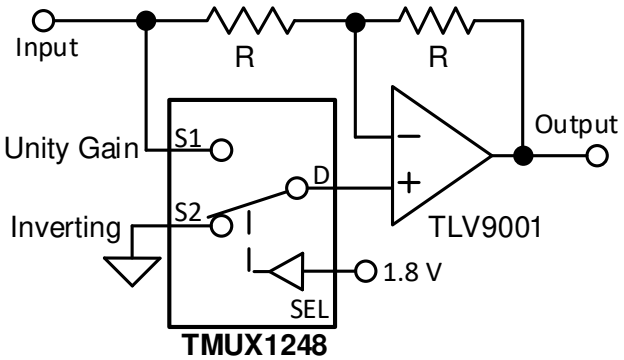
製品情報(1)

部品番号	パッケージ	本体サイズ (公称)
TMUX1248	SC70 (6)	2.00mm × 1.25mm

(1) 提供されているすべてのパッケージについては、データシートの末尾にあるパッケージ・オプションについての付録を参照してください。



TMUX1248 ブロック図



アプリケーションの例

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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

DATE	REVISION	NOTES
July 2021	*	Initial Release

5 Pin Configuration and Functions

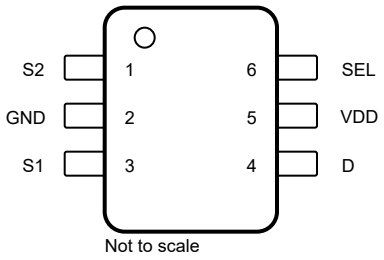


図 5-1. DCK Package 6-Pin SC70 Top View

表 5-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION(2)
NAME	NO.		
D	4	I/O	Drain pin. Can be an input or output.
GND	2	P	Ground (0 V) reference.
S1	3	I/O	Source pin 1. Can be an input or output.
S2	1	I/O	Source pin 2. Can be an input or output.
SEL	6	I	Select pin: controls state of the switch according to 表 8-1.
V_{DD}	5	P	Positive power supply. This pin is the most positive power-supply potential. For reliable operation, connect a decoupling capacitor ranging from 0.1 µF to 10 µF between V_{DD} and GND.

(1) I = input, O = output, I/O = input and output, P = power.
(2) Refer to セクション 8.4 for what to do with unused pins.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2) (3)

		MIN	MAX	UNIT
V_{DD}	Supply voltage	–0.5	6	V
V_{SEL} or V_{EN}	Logic control input pin voltage (SEL)	–0.5	6	V
I_{SEL} or I_{EN}	Logic control input pin current (SEL)	–30	30	mA
V_S or V_D	Source or drain voltage (Sx, D)	–0.5	V_{DD}+0.5	V
I_S or $I_{D\ (CONT)}$	Source or drain continuous current (Sx, D)	–50	50	mA
I_K	Diode clamp current(4)	–30	30	mA
T_{stg}	Storage temperature	–65	150	°C
T_J	Junction temperature		150	°C

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
(3) All voltages are with respect to ground, unless otherwise specified.
(4) Pins are diode-clamped to the power-supply rails. Over voltage signals must be voltage and current limited to maximum ratings.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±750	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{DD}	Supply voltage	1.08		5.5	V
V_S or V_D	Signal path input/output voltage (source or drain pin) (Sx, D)	0		V_{DD}	V
V_{SEL}	Logic control input pin voltage (SEL)	0		5.5	V
T_A	Ambient temperature	–40		125	°C
t_r,t_f	Logic input pin rise and fall time			70	ns/V

6.4 Thermal Information

THERMAL METRIC(1)		TMUX1248 DCK (SC70) 6 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	243.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	180.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	106.3	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	89.1	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	106.0	°C/W

6.4 Thermal Information (continued)

THERMAL METRIC(1)		TMUX1248 DCK (SC70) 6 PINS	UNIT
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics (V_{DD} = 5 V ±10 %), GND = 0 V unless otherwise specified.

at T_A = 25°C, V_{DD} = 5 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = 0 V to V_{DD} I_{SD} = 10 mA	25°C		3		Ω
			–40°C to +85°C			5	Ω
			–40°C to +125°C			6	Ω
ΔR_{ON}	On-resistance matching between channels	V_S = 0 V to V_{DD} I_{SD} = 10 mA	25°C		0.15		Ω
			–40°C to +85°C			1	Ω
			–40°C to +125°C			1	Ω
$R_{ON\ FLAT}$	On-resistance flatness	V_S = 0 V to V_{DD} I_{SD} = 10 mA	25°C		1.5		Ω
			–40°C to +85°C		2		Ω
			–40°C to +125°C		3		Ω
$I_{S(OFF)}$	Source off leakage current(1)	V_{DD} = 5 V Switch Off V_D = 4.5 V / 1.5 V V_S = 1.5 V / 4.5 V	25°C		±75		nA
			–40°C to +85°C	–150		150	nA
			–40°C to +125°C	–175		175	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	V_{DD} = 5 V Switch On V_D = V_S = 4.5 V / 1 V	25°C		±200		nA
			–40°C to +85°C	–500		500	nA
			–40°C to +125°C	–750		750	nA
LOGIC INPUTS							
V_{IH}	Input logic high		-40°C to 125°C	1.42		5.5	V
V_{IL}	Input logic low		-40°C to 125°C	0		0.87	V
I_{IH} I_{IL}	Input leakage current		25°C		±0.005		µA
I_{IH} I_{IL}	Input leakage current		–40°C to +125°C			±0.05	µA
C_{IN}	Digital input capacitance		25°C		1		pF
C_{IN}	Digital input capacitance		–40°C to +125°C			2	pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Digital Inputs = 0 V or 5.5 V	25°C		0.007		µA
			–40°C to +125°C			1.5	µA

6.5 Electrical Characteristics (V_{DD} = 5 V ±10 %), GND = 0 V unless otherwise specified. (continued)

at T_A = 25°C, V_{DD} = 5 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Switching time between channels	V_S = 3 V R_L = 200 Ω, C_L = 15 pF	25°C		12		ns
			–40°C to +85°C			18	ns
			–40°C to +125°C			19	ns
t_{OPEN} (BBM)	Break before make time	V_S = 3 V R_L = 200 Ω, C_L = 15 pF	25°C		8		ns
			–40°C to +85°C	1			ns
			–40°C to +125°C	1			ns
Q_C	Charge Injection	V_S = V_{DD} /2 R_S = 0 Ω, C_L = 1 nF	25°C		–10		pC
O_{ISO}	Off Isolation	R_L = 50 Ω, C_L = 5 pF f = 1 MHz	25°C		–65		dB
		R_L = 50 Ω, C_L = 5 pF f = 10 MHz	25°C		–45		dB
X_{TALK}	Crosstalk	R_L = 50 Ω, C_L = 5 pF f = 1 MHz	25°C		–65		dB
		R_L = 50 Ω, C_L = 5 pF f = 10 MHz	25°C		–45		dB
BW	Bandwidth	R_L = 50 Ω, C_L = 5 pF	25°C		250		MHz
C_{SOFF}	Source off capacitance	f = 1 MHz	25°C		7		pF
C_{SON} C_{DON}	On capacitance	f = 1 MHz	25°C		23		pF

(1) When V_S is 4.5 V, V_D is 1.5 V or when V_S is 1.5 V, V_D is 4.5 V.

6.6 Electrical Characteristics (V_{DD} = 3.3 V ±10 %), GND = 0 V unless otherwise specified.

at T_A = 25°C, V_{DD} = 3.3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = 0 V to V_{DD} I_{SD} = 10 mA	25°C		4.5		Ω
			–40°C to +85°C			12.5	Ω
			–40°C to +125°C			13	Ω
ΔR_{ON}	On-resistance matching between channels	V_S = 0 V to V_{DD} I_{SD} = 10 mA	25°C		0.15		Ω
			–40°C to +85°C			1	Ω
			–40°C to +125°C			1	Ω
$R_{ON\ FLAT}$	On-resistance flatness	V_S = 0 V to V_{DD} I_{SD} = 10 mA	25°C		3.5		Ω
			–40°C to +85°C		4		Ω
			–40°C to +125°C		5		Ω
$I_{S(OFF)}$	Source off leakage current(1)	V_{DD} = 3.3 V Switch Off V_D = 3 V / 1 V V_S = 1 V / 3 V	25°C		±75		nA
			–40°C to +85°C	–150		150	nA
			–40°C to +125°C	–175		175	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	V_{DD} = 3.3 V Switch On V_D = V_S = 3 V / 1 V	25°C		±200		nA
			–40°C to +85°C	–500		500	nA
			–40°C to +125°C	–750		750	nA
LOGIC INPUTS							
V_{IH}	Input logic high		-40°C to 125°C	1.3		5.5	V
V_{IL}	Input logic low		-40°C to 125°C	0		0.8	V
I_{IH} I_{IL}	Input leakage current		25°C		±0.005		µA
I_{IH} I_{IL}	Input leakage current		–40°C to +125°C			±0.05	µA
C_{IN}	Logic input capacitance		25°C		1		pF
C_{IN}	Logic input capacitance		–40°C to +125°C			2	pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Digital Inputs = 0 V or 5.5 V	25°C		0.004		µA
			–40°C to +125°C			0.8	µA

6.6 Electrical Characteristics (V_{DD} = 3.3 V ±10 %), GND = 0 V unless otherwise specified. (continued)

at T_A = 25°C, V_{DD} = 3.3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Switching time between channels	V_S = 2 V R_L = 200 Ω, C_L = 15 pF	25°C		14		ns
			–40°C to +85°C			20	ns
			–40°C to +125°C			22	ns
t_{OPEN} (BBM)	Break before make time	V_S = 2 V R_L = 200 Ω, C_L = 15 pF	25°C		8		ns
			–40°C to +85°C	1			ns
			–40°C to +125°C	1			ns
Q_C	Charge Injection	V_S = V_{DD}/2 R_S = 0 Ω, C_L = 1 nF	25°C		–6		pC
O_{ISO}	Off Isolation	R_L = 50 Ω, C_L = 5 pF f = 1 MHz	25°C		–65		dB
		R_L = 50 Ω, C_L = 5 pF f = 10 MHz	25°C		–45		dB
X_{TALK}	Crosstalk	R_L = 50 Ω, C_L = 5 pF f = 1 MHz	25°C		–65		dB
		R_L = 50 Ω, C_L = 5 pF f = 10 MHz	25°C		–45		dB
BW	Bandwidth	R_L = 50 Ω, C_L = 5 pF	25°C		250		MHz
C_{SOFF}	Source off capacitance	f = 1 MHz	25°C		7		pF
C_{SON} C_{DON}	On capacitance	f = 1 MHz	25°C		23		pF

(1) When V_S is 3 V, V_D is 1 V or when V_S is 1 V, V_D is 3 V.

6.7 Electrical Characteristics (V_{DD} = 1.8 V ±10 %), GND = 0 V unless otherwise specified.

at T_A = 25°C, V_{DD} = 1.8 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = 0 V to V_{DD} I_{SD} = 10 mA	25°C		40		Ω
			–40°C to +85°C			80	Ω
			–40°C to +125°C			80	Ω
ΔR_{ON}	On-resistance matching between channels	V_S = 0 V to V_{DD} I_{SD} = 10 mA	25°C		0.4		Ω
			–40°C to +85°C			1.5	Ω
			–40°C to +125°C			1.5	Ω
$R_{ON\ FLAT}$	On-resistance flatness	V_S = 0 V to V_{DD} I_{SD} = 10 mA	25°C		35		Ω
$I_{S(OFF)}$	Source off leakage current(1)	V_{DD} = 1.98 V Switch Off V_D = 1.8 V / 1 V V_S = 1 V / 1.8 V	25°C		±75		nA
			–40°C to +85°C	–150		150	nA
			–40°C to +125°C	–175		175	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	V_{DD} = 1.98 V Switch On V_D = V_S = 1.62 V / 1 V	25°C		±200		nA
			–40°C to +85°C	–500		500	nA
			–40°C to +125°C	–750		750	nA
DIGITAL INPUTS							
V_{IH}	Input logic high		–40°C to +125°C	1.07		5.5	V
V_{IL}	Input logic low		–40°C to +125°C	0		0.68	V
I_{IH} I_{IL}	Input leakage current		25°C		±0.005		µA
I_{IH} I_{IL}	Input leakage current		–40°C to +125°C			±0.05	µA
C_{IN}	Logic input capacitance		25°C		1		pF
C_{IN}	Logic input capacitance		–40°C to +125°C			2	pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Logic Inputs = 0 V or 5.5 V	25°C		0.002		µA
			–40°C to +125°C			0.52	µA

6.7 Electrical Characteristics (V_{DD} = 1.8 V ±10 %), GND = 0 V unless otherwise specified. (continued)

at T_A = 25°C, V_{DD} = 1.8 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Switching time between channels	V_S = 1 V R_L = 200 Ω, C_L = 15 pF	25°C		24		ns
			–40°C to +85°C			44	ns
			–40°C to +125°C			45	ns
t_{OPEN} (BBM)	Break before make time	V_S = 1 V R_L = 200 Ω, C_L = 15 pF	25°C		16		ns
			–40°C to +85°C	1			ns
			–40°C to +125°C	1			ns
Q_C	Charge Injection	V_S = V_{DD}/2 R_S = 0 Ω, C_L = 1 nF	25°C		–3		pC
O_{ISO}	Off Isolation	R_L = 50 Ω, C_L = 5 pF f = 1 MHz	25°C		–65		dB
		R_L = 50 Ω, C_L = 5 pF f = 10 MHz	25°C		–45		dB
X_{TALK}	Crosstalk	R_L = 50 Ω, C_L = 5 pF f = 1 MHz	25°C		–65		dB
		R_L = 50 Ω, C_L = 5 pF f = 10 MHz	25°C		–45		dB
BW	Bandwidth	R_L = 50 Ω, C_L = 5 pF	25°C		250		MHz
C_{SOFF}	Source off capacitance	f = 1 MHz	25°C		7		pF
C_{SON} C_{DON}	On capacitance	f = 1 MHz	25°C		23		pF

(1) When V_S is 1.8 V, V_D is 1 V or when V_S is 1 V, V_D is 1.8 V.

6.8 Electrical Characteristics (V_{DD} = 1.2 V ±10 %), GND = 0 V unless otherwise specified.

at T_A = 25°C, V_{DD} = 1.2 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
ANALOG SWITCH							
R_{ON}	On-resistance	V_S = 0 V to V_{DD} I_{DS} = 10 mA	25°C		70		Ω
			–40°C to +85°C			105	Ω
			–40°C to +125°C			105	Ω
ΔR_{ON}	On-resistance matching between channels	V_S = 0 V to V_{DD} I_{DS} = 10 mA	25°C		0.4		Ω
			–40°C to +85°C			1.5	Ω
			–40°C to +125°C			1.5	Ω
$R_{ON\ FLAT}$	On-resistance flatness	V_S = 0 V to V_{DD} I_{DS} = 10 mA	25°C		65		Ω
$I_{S(OFF)}$	Source off leakage current(1)	V_{DD} = 1.32 V Switch Off V_D = 1.2 V / 1 V V_S = 1 V / 1.2 V	25°C		±75		nA
			–40°C to +85°C	–150		150	nA
			–40°C to +125°C	–175		175	nA
$I_{D(ON)}$ $I_{S(ON)}$	Channel on leakage current	V_{DD} = 1.32 V Switch On V_D = V_S = 1 V / 0.8 V	25°C		±200		nA
			–40°C to +85°C	–500		500	nA
			–40°C to +125°C	–750		750	nA
DIGITAL INPUTS							
V_{IH}	Input logic high		–40°C to +125°C	0.96			V
V_{IL}	Input logic low		–40°C to +125°C			0.36	V
I_{IH} I_{IL}	Input leakage current		25°C		±0.005		µA
I_{IH} I_{IL}	Input leakage current		–40°C to +125°C			±0.10	µA
C_{IN}	Digital input capacitance		25°C		1		pF
C_{IN}	Digital input capacitance		–40°C to +125°C			2	pF
POWER SUPPLY							
I_{DD}	V_{DD} supply current	Digital Inputs = 0 V or 5.5 V	25°C		0.0015		µA
			–40°C to +125°C			0.45	µA

6.8 Electrical Characteristics (V_{DD} = 1.2 V ±10 %), GND = 0 V unless otherwise specified. (continued)

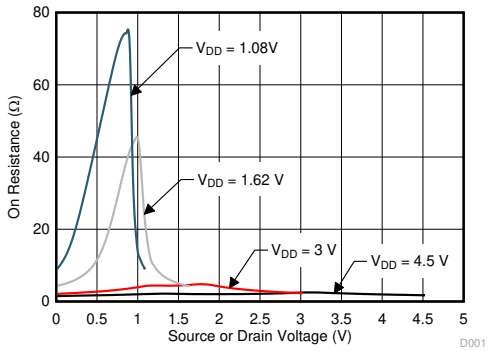
at T_A = 25°C, V_{DD} = 1.2 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
DYNAMIC CHARACTERISTICS							
t_{TRAN}	Switching time between channels	V_{IN} = V_{DD} V_S = 1 V R_L = 200 Ω, C_L = 15 pF	25°C		40		ns
			–40°C to +85°C			175	ns
			–40°C to +125°C			175	ns
t_{OPEN} (BBM)	Break before make time	V_S = 1 V R_L = 200 Ω, C_L = 15 pF	25°C		27		ns
			–40°C to +85°C	1			ns
			–40°C to +125°C	1			ns
Q_C	Charge Injection	V_S = (V_{DD} + V_{SS})/2 R_S = 0 Ω, C_L = 1 nF	25°C		±5		pC
O_{ISO}	Off Isolation	R_L = 50 Ω, C_L = 5 pF f = 1 MHz	25°C		–64		dB
		R_L = 50 Ω, C_L = 5 pF f = 10 MHz	25°C		–44		dB
X_{TALK}	Crosstalk	R_L = 50 Ω, C_L = 5 pF f = 1 MHz	25°C		–64		dB
		R_L = 50 Ω, C_L = 5 pF f = 10 MHz	25°C		–44		dB
BW	Bandwidth	R_L = 50 Ω, C_L = 5 pF	25°C		250		MHz
C_{SOFF}	Source off capacitance	f = 1 MHz	25°C		7		pF
C_{SON} C_{DON}	On capacitance	f = 1 MHz	25°C		23		pF

(1) When V_S is 1 V, V_D is 1.2 V or when V_S is 1.2 V, V_D is 1 V.

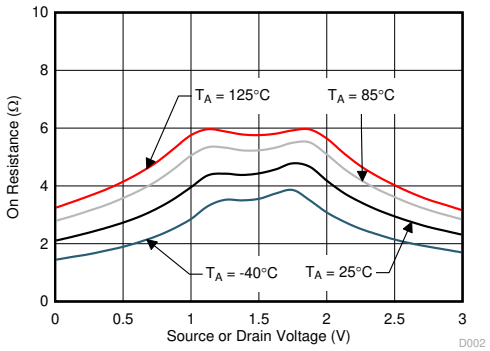
6.9 Typical Characteristics

At T_A = 25°C, V_{DD} = 5 V (unless otherwise noted).



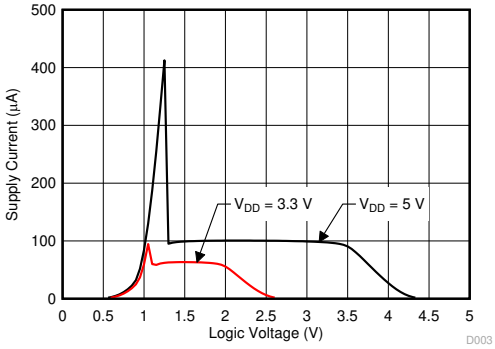
T_A = 25°C

図 6-1. On-Resistance vs Source or Drain Voltage



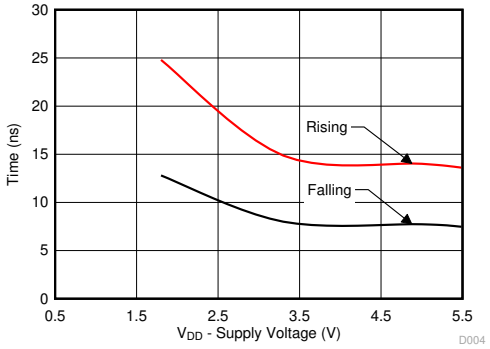
V_{DD} = 3 V

図 6-2. On-Resistance vs Source or Drain Voltage



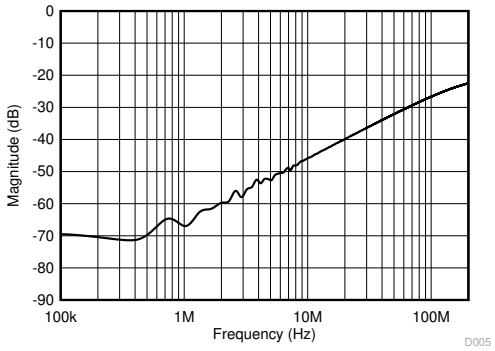
T_A = 25°C

図 6-3. Supply Current vs Logic Voltage



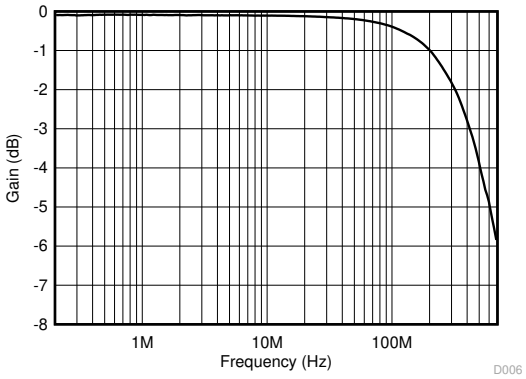
T_A = 25°C

図 6-4. $T_{transition}$ vs Supply Voltage



T_A = 25°C

図 6-5. Crosstalk and Off-Isolation vs Frequency



T_A = 25°C

図 6-6. Frequency Response

7 Parameter Measurement Information

7.1 On-Resistance

The on-resistance of a device is the ohmic resistance between the source (Sx) and drain (D) pins of the device. The on-resistance varies with input voltage and supply voltage. The symbol R_{ON} is used to denote on-resistance. The measurement setup used to measure R_{ON} is shown in 図 7-1. Voltage (V) and current (I_{SD}) are measured using this setup, and R_{ON} is computed with $R_{ON} = V / I_{SD}$:

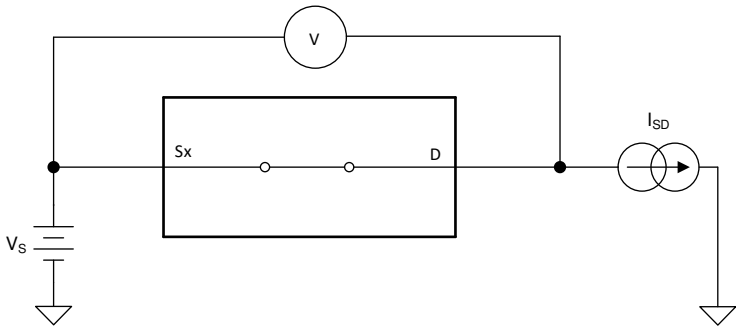


図 7-1. On-Resistance Measurement Setup

7.2 Off-Leakage Current

Source leakage current is defined as the leakage current flowing into or out of the source pin when the switch is off. This current is denoted by the symbol $I_{S(OFF)}$.

The setup used to measure off-leakage current is shown in 図 7-2.

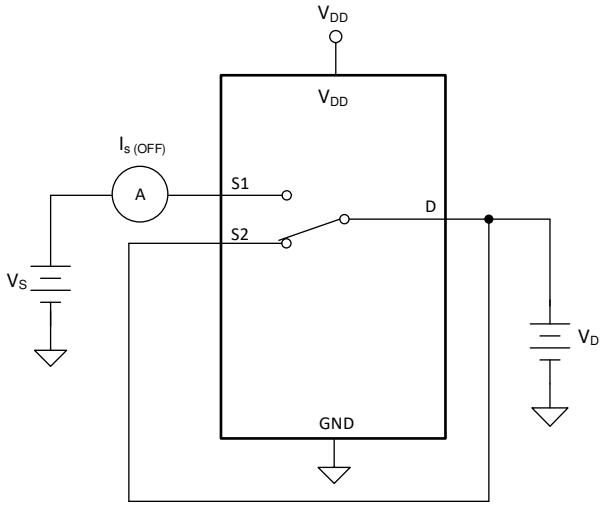


図 7-2. Off-Leakage Measurement Setup

7.3 On-Leakage Current

Source on-leakage current is defined as the leakage current flowing into or out of the source pin when the switch is on. This current is denoted by the symbol $I_{S(ON)}$.

Drain on-leakage current is defined as the leakage current flowing into or out of the drain pin when the switch is on. This current is denoted by the symbol $I_{D(ON)}$.

Either the source pin or drain pin is left floating during the measurement. 図 7-3 shows the circuit used for measuring the on-leakage current, denoted by $I_{S(ON)}$ or $I_{D(ON)}$.

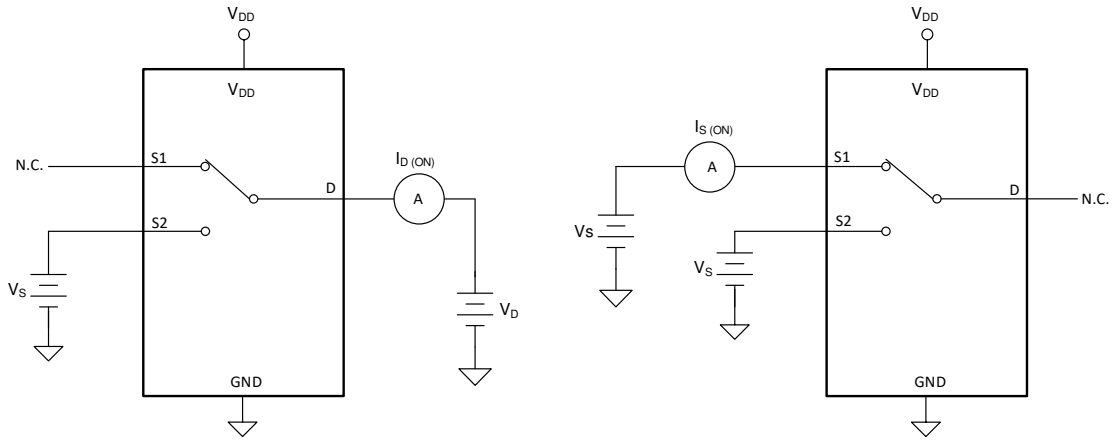


図 7-3. On-Leakage Measurement Setup

7.4 Transition Time

Transition time is defined as the time taken by the output of the device to rise or fall 10% after the logic control signal has risen or fallen past the logic threshold. The 10% transition measurement is utilized to provide the timing of the device. System level timing can then account for the time constant added from the load resistance and load capacitance. 図 7-4 shows the setup used to measure transition time, denoted by the symbol $t_{TRANSITION}$.

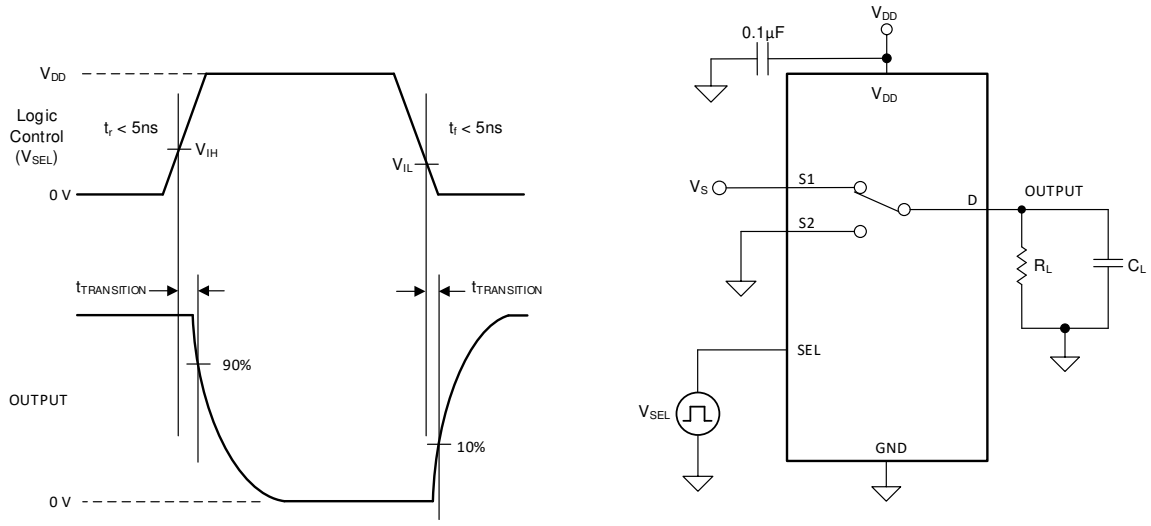


図 7-4. Transition-Time Measurement Setup

7.5 Break-Before-Make

Break-before-make delay is a safety feature that prevents two inputs from connecting when the device is switching. The output first breaks from the on-state switch before making the connection with the next on-state switch. The time delay between the *break* and the *make* is known as break-before-make delay. 図 7-5 shows the setup used to measure break-before-make delay, denoted by the symbol $t_{OPEN(BBM)}$.

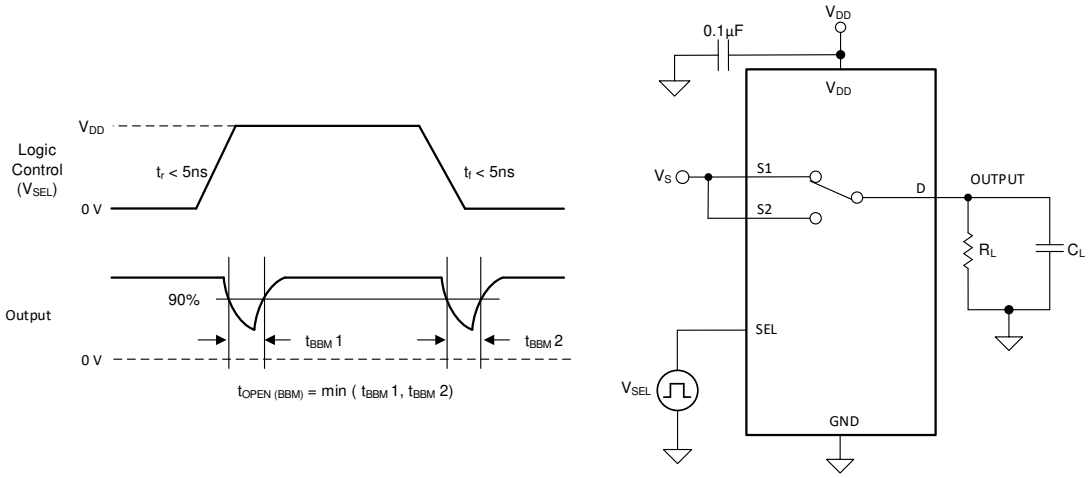


図 7-5. Break-Before-Make Delay Measurement Setup

7.6 Charge Injection

The TMUX1248 has a transmission-gate topology. Any mismatch in capacitance between the NMOS and PMOS transistors results in a charge injected into the drain or source during the falling or rising edge of the gate signal. The amount of charge injected into the source or drain of the device is known as charge injection, and is denoted by the symbol Q_C. 図 7-6 shows the setup used to measure charge injection from Drain (D) to Source (Sx).

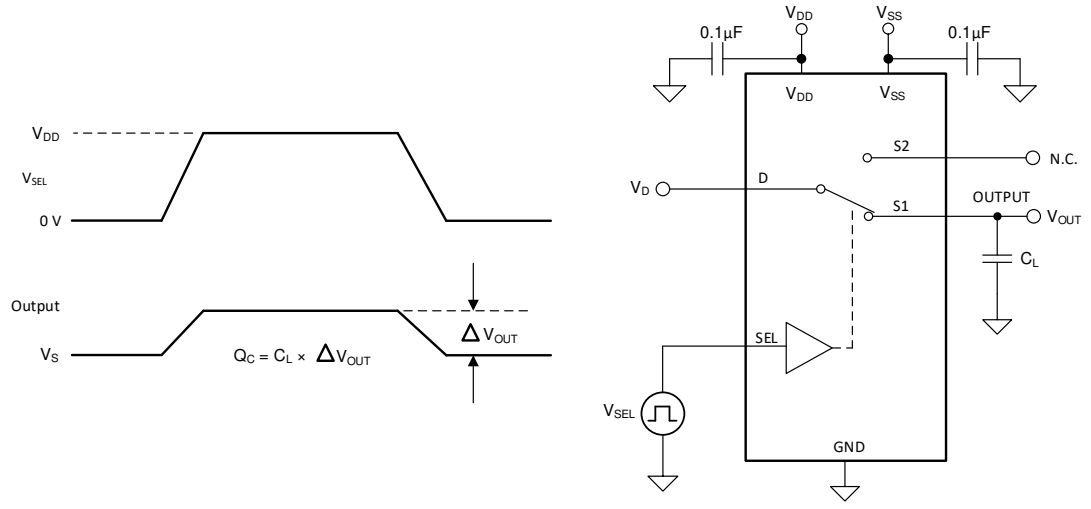


図 7-6. Charge-Injection Measurement Setup

7.7 Off Isolation

Off isolation is defined as the ratio of the signal at the drain pin (D) of the device when a signal is applied to the source pin (Sx) of an off-channel. 図 7-7 shows the setup used to measure, and the equation used to calculate off isolation.

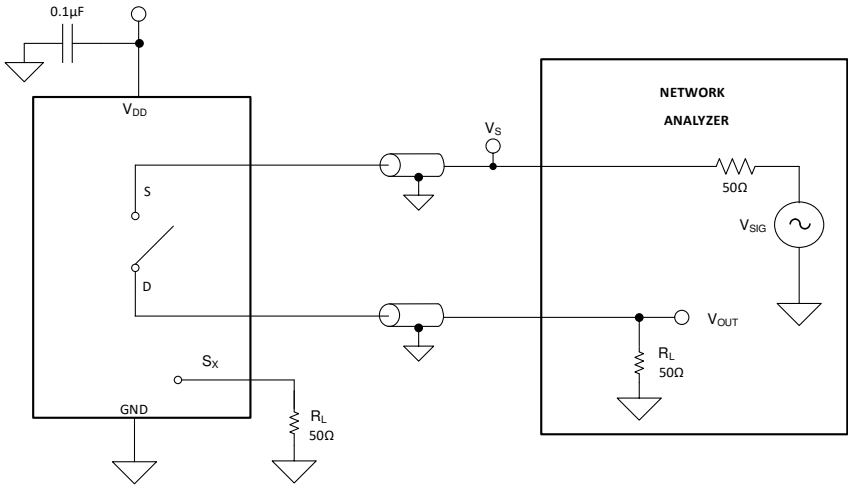


図 7-7. Off Isolation Measurement Setup

$$\text{Off Isolation} = 20 \cdot \text{Log}\left(\frac{V_{OUT}}{V_S}\right) \quad (1)$$

7.8 Crosstalk

Crosstalk is defined as the ratio of the signal at the drain pin (D) of a different channel, when a signal is applied at the source pin (Sx) of an on-channel. 図 7-8 shows the setup used to measure, and the equation used to calculate crosstalk.

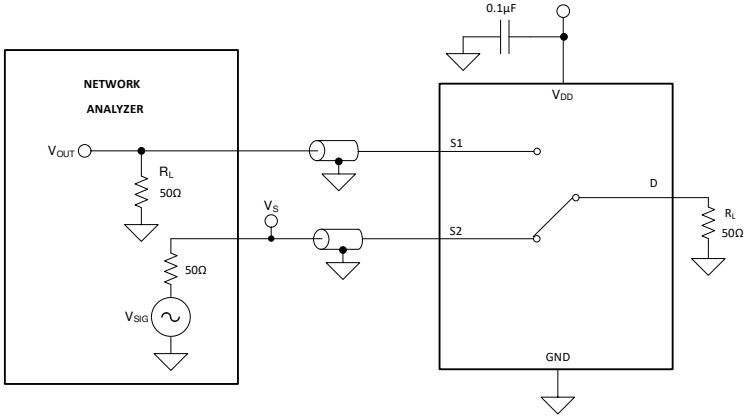


図 7-8. Crosstalk Measurement Setup

$$\text{Channel-to-Channel Crosstalk} = 20 \cdot \text{Log}\left(\frac{V_{OUT}}{V_S}\right) \quad (2)$$

7.9 Bandwidth

Bandwidth is defined as the range of frequencies that are attenuated by less than 3 dB when the input is applied to the source pin (Sx) of an on-channel, and the output is measured at the drain pin (D) of the device. 図 7-9 shows the setup used to measure bandwidth.

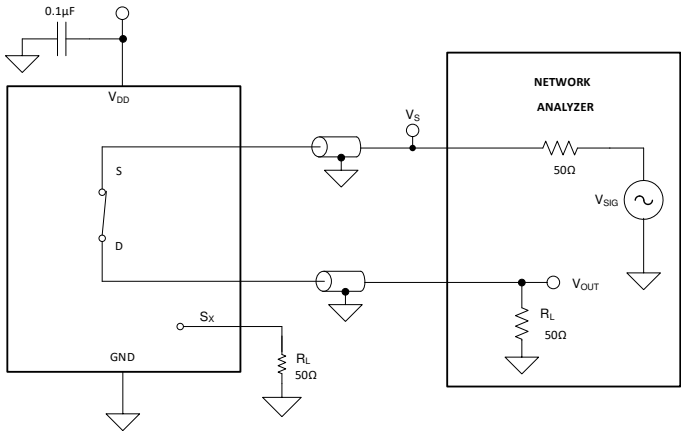


図 7-9. Bandwidth Measurement Setup

8 Detailed Description

8.1 Overview

The TMUX1248 is a 2:1 (SPDT), 1-channel switch where the input is controlled with a single select (SEL) control pin.

8.2 Functional Block Diagram

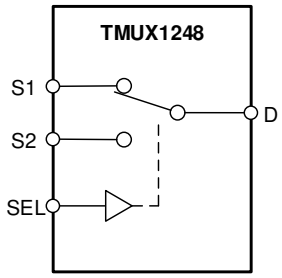


図 8-1. TMUX1248 Functional Block Diagram

8.3 Feature Description

8.3.1 Bidirectional Operation

The TMUX1248 conducts equally well from source (Sx) to drain (D) or from drain (D) to source (Sx). The device has very similar characteristics in both directions and supports both analog and digital signals.

8.3.2 Rail to Rail Operation

The valid signal path input/output voltage for TMUX1248 ranges from GND to V_{DD}.

8.3.3 1.8 V Logic Compatible Inputs

The TMUX1248 has 1.8 V logic compatible control for the logic control input (SEL). The logic input threshold scales with supply but still provides 1.8 V logic control when operating at 5.5 V supply voltage. 1.8 V logic level inputs allow the TMUX1248 to interface with processors that have lower logic I/O rails and eliminates the need for an external translator, which saves both space and BOM cost. For more information on 1.8 V logic implementations refer to *Simplifying Design with 1.8 V logic Muxes and Switches*.

8.3.4 Fail-Safe Logic

The TMUX1248 supports Fail-Safe Logic on the control input pin (SEL) allowing for operation up to 5.5 V, regardless of the state of the supply pin. This feature allows voltages on the control pin to be applied before the supply pin, or allows higher voltages on the SEL pin up to 5.5 V, protecting the device from potential damage. Fail-Safe Logic minimizes system complexity by removing the need for power supply sequencing on the logic control pin. For example, the Fail-Safe Logic feature allows the select pin of the TMUX1248 to be ramped to 5.5 V while V_{DD} = 0 V. Additionally, the feature enables operation of the TMUX1248 with V_{DD} = 1.2 V while allowing the select pin to interface with a logic level of another device up to 5.5 V.

8.4 Device Functional Modes

The select (SEL) pin of the TMUX1248 controls which switch is connected to the drain of the device. When a given input is not selected, that source pin is in high impedance mode (HI-Z). The control pins can be as high as 5.5 V.

The TMUX1248 can be operated without any external components except for the supply decoupling capacitors. Unused logic control pins should be tied to GND or V_{DD} in order to ensure the device does not consume additional current as highlighted in *Implications of Slow or Floating CMOS Inputs*. Unused signal path inputs (Sx or D) should be connected to GND.

8.5 Truth Tables

表 8-1. TMUX1248 Truth Table

CONTROL LOGIC (SEL)	Selected Source (Sx) Connected To Drain (D) Pin
0	S1
1	S2

Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The TMUX12xx family offers good system performance across a wide operating supply (1.08 V to 5.5 V). These devices include 1.8 V logic compatible control input pins that enable operation in systems with 1.8 V I/O rails. Additionally, the control input pin supports Fail-Safe Logic which allows for operation up to 5.5 V, regardless of the state of the supply pin. This protection stops the logic pins from back-powering the supply rail. These features of the TMUX12xx, a family of general purpose multiplexers and switches, reduce system complexity, board size, and overall system cost.

9.2 Typical Application

9.2.1 Switchable Operational Amplifier Gain Setting

Another example application of the TMUX1248 is to change an Op Amp from unity gain setting to an inverting amplifier configuration. Utilizing a switch allows a system to have a configurable gain and allows the same architecture to be utilized across the board for various inputs to the system. 図 9-1 shows the TMUX1248 configured for gain setting application.

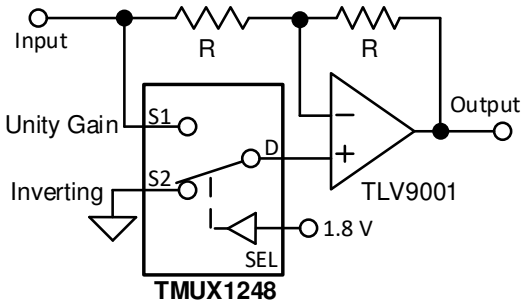


図 9-1. Switchable Op Amp Gain Setting

9.2.1.1 Design Requirements

This design example uses the parameters listed in 表 9-1.

表 9-1. Design Parameters

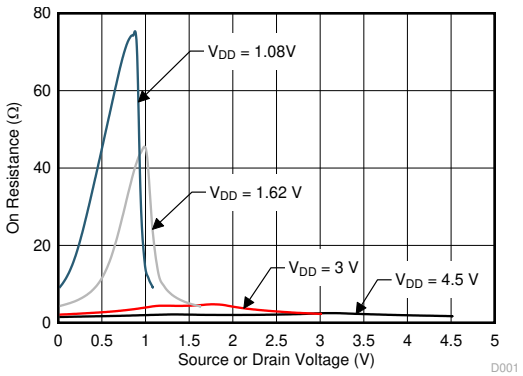
PARAMETERS	VALUES
Input Signal	0 V to 2.75 V
Mux Supply (V_{DD})	2.75 V
Op Amp Supply (V_+/ V_-)	±2.75 V
Mux I/O signal range	0 V to V_{DD} (Rail to Rail)
Control logic thresholds	1.8 V compatible (up to 5.5 V)

9.2.1.2 Detailed Design Procedure

The application shown in 図 9-1 demonstrates how to use a single control input and toggle between gain settings of -1 and +1. If switching between inverting and unity gain is not required, the TMUX1248 can be utilized in the feedback path to select different feedback resistors and provide scalable gain settings for configurable signal conditioning.

The TMUX1248 can be operated without any external components except for the supply decoupling capacitors. The select pin is recommended to have a pull-down or pull-up resistor to ensure the input is in a known state if the control signal becomes disconnected. All inputs to the switch must fall within the recommend operating conditions of the TMUX1248 including signal range and continuous current. For this design with a supply of 2.75 V the signal range can be 0 V to 2.75 V and the max continuous current can be 50 mA.

9.2.1.3 Application Curve



T_A = 25°C

図 9-2. On-Resistance vs Source or Drain Voltage

9 Power Supply Recommendations

The TMUX1248 operates across a wide supply range of 1.08 V to 5.5 V. Do not exceed the absolute maximum ratings because stresses beyond the listed ratings can cause permanent damage to the devices.

Power-supply bypassing improves noise margin and prevents switching noise propagation from the V_{DD} supply to other components. Good power-supply decoupling is important to achieve optimum performance. For improved supply noise immunity, use a supply decoupling capacitor ranging from 0.1 µF to 10 µF from V_{DD} to ground. Place the bypass capacitors as close to the power supply pins of the device as possible using low-impedance connections. TI recommends using multi-layer ceramic chip capacitors (MLCCs) that offer low equivalent series resistance (ESR) and inductance (ESL) characteristics for power-supply decoupling purposes. For very sensitive systems, or for systems in harsh noise environments, avoiding the use of vias for connecting the capacitors to the device pins may offer superior noise immunity. The use of multiple vias in parallel lowers the overall inductance and is beneficial for connections to ground planes.

10 Layout

10.1 Layout Guidelines

10.1.1 Layout Information

When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection primarily occurs because the width of the trace changes. At the apex of the turn, the trace width increases to 1.414 times its width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. 図 10-1 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

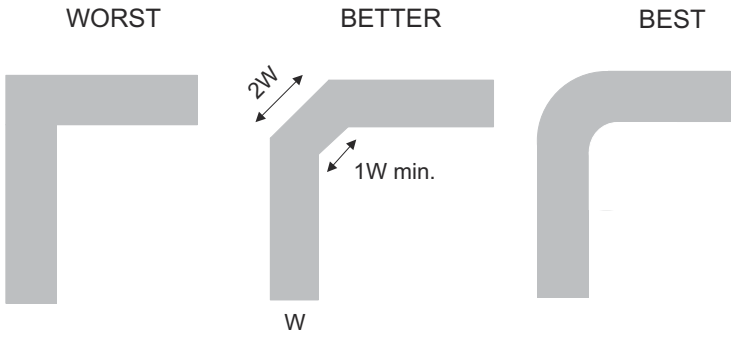


図 10-1. Trace Example

Route high-speed signals using a minimum of vias and corners which reduces signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the signal's transmission line and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points, through-hole pins are not recommended at high frequencies.

図 10-2 illustrates an example of a PCB layout with the TMUX1248. Some key considerations are:

- Decouple the V_{DD} pin with a 0.1-µF capacitor, placed as close to the pin as possible. Make sure that the capacitor voltage rating is sufficient for the V_{DD} supply.
- Keep the input lines as short as possible.
- Use a solid ground plane to help reduce electromagnetic interference (EMI) noise pickup.
- Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when necessary.

10.2 Layout Example

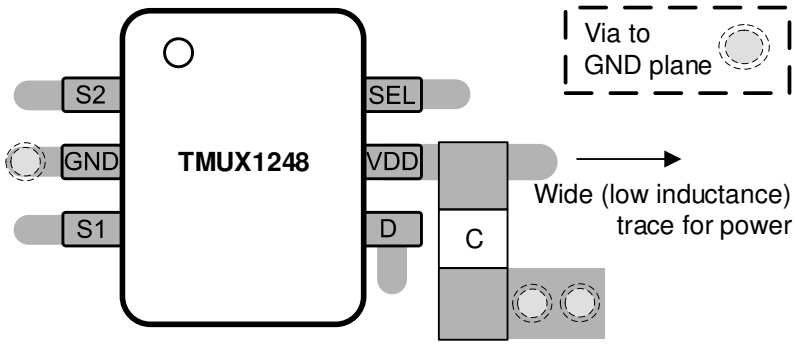


図 10-2. TMUX1248 Layout Example

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *Improve Stability Issues with Low CON Multiplexers* application brief
- Texas Instruments, *Simplifying Design with 1.8 V logic Muxes and Switches* application brief
- Texas Instruments, *Eliminate Power Sequencing with Powered-off Protection Signal Switches* application brief
- Texas Instruments, *System-Level Protection for High-Voltage Analog Multiplexers* application reports

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 サポート・リソース

TI E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

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11.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
すべての商標は、それぞれの所有者に帰属します。

11.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.6 Glossary

TI Glossary — This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TMUX1248DCKR	Active	Production	SC70 (DCK) | 6	3000 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	248
TMUX1248DCKR.A	Active	Production	SC70 (DCK) | 6	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	248

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

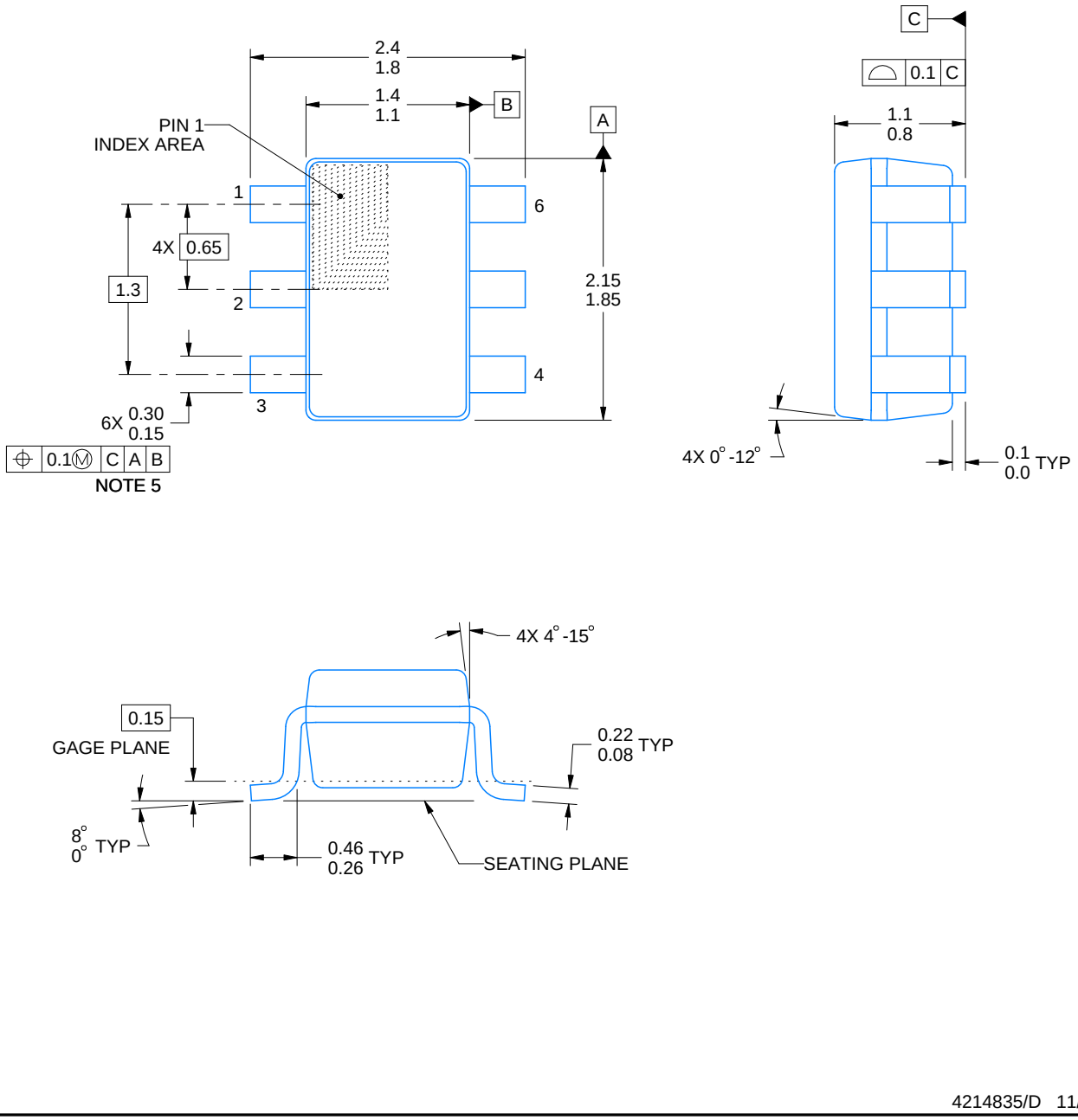
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

PACKAGE OUTLINE

DCK0006A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



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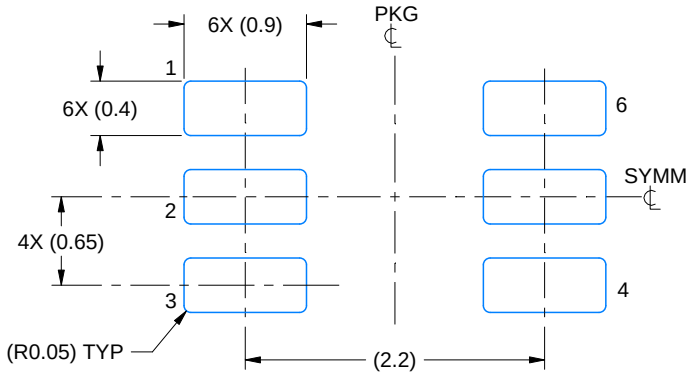
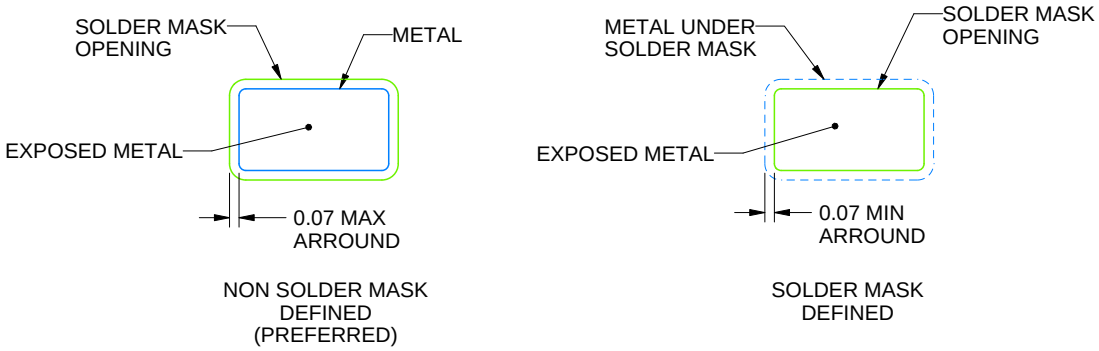
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
4. Falls within JEDEC MO-203 variation AB.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

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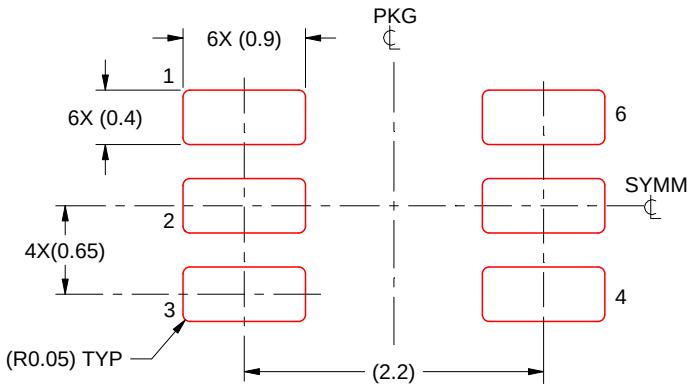
NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214835/D 11/2024

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

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